CdS photoconductive cell Resin coating type (5R type)



Standard type designed for general-purpose, wide application

CdS photoconductive cells utilize photoconductive effects in semiconductors that decrease their resistance when illuminated by light. These sensors are non-polar resistive elements with spectral response characteristics close to the human eye (luminous efficiency), thus making their operating circuits simple and small.

Features

- Small size, thin package
- Low price
- Wide range of sensor lineup

Applications

- Programed electronic shutter and stroboscope light control for compact camera
- Auto dimmer for digital display, CRT and room illumination
- Sensor for automatic light on/off
- Sensor for electronic toy and teaching aid material

Absolute maximum ratings / Characteristics (Typ. Ta=25 °C, unless otherwise noted)

| Type No. | Absolute maximum ratings | | | Characteristics *1 | | | | | | |
|----------|----------------------------|--------------------------|--------------------------------------|---|--------------------|--------------|--------------|--------------|------------------------|-----------------|
| | Supply voltage (Vdc) | Power dissipation P (mW) | Ambient temperature Ta (°C) | Peak sensitivity wavelength λp (nm) | Cell resistance *2 | | | | Response time 10 Lx *5 | |
| | | | | | | | 0 lx *3 | γ±0 *4 | Rise time tr | Fall time tf |
| | | | | | Min. (kΩ) | Max. (kΩ) | Min. (MΩ) | 100 to 10 Lx | (ms) | (ms) |
| P687-02 | 100 | 30 | -30 to +50 | 620 | 5 | 20 | 5.0 | 0.70 | 60 | 25 |
| P1201-04 | | 50 | -30 to +60 | 540 | 50 | 200 | 20 | 0.90 | 40 | 30 |
| P1201-06 | | | | | 50 | 100 | | | | |
| P1241-04 | 50 | 30 | -30 to +60 | 560 | 3 | 9 | 0.2 | 0.70 | | 40 |
| P1241-05 | | | | | 8 | 24 | 0.5 | 0.70 | 50 | |
| P1241-06 | | | | | 5 | 20 | 0.5 | 0.75 | | |
| P1444 | 100 | | -30 to +50 | 620 | 10 | 50 | 5.0 | 0.85 | 40 | 10 |
| P1445 | | | | | 48 | 140 | 20 | | | |

^{*1:} All characteristics are measured after exposure to light (100 to 500 lx) for one to two hours.

$$\gamma_{100}^{100} = \frac{\log (R_{100}) - \log (R_{10})}{\log (E_{100}) - \log (E_{10})}$$

E100, E10: illuminance 100 lx, 10 lx

R100, R10 resistance at 100 lx and 10 lx respectively

*5: The rise time is the time required for the sensor resistance to reach 63 % of the saturated conductance level (when fully illuminated). The fall time is the time required for the sensor resistance to decay from the saturated conductance level to 37 %.



^{*2:} The light source is a standard tungsten lamp operated at a color temperature of 2856 K.

^{*3:} Measured 10 seconds after shutting off the 10 lx light.

^{*4:} Typical gamma characteristics (within ±0.10 variations) between 100 lx to 10 lx